# MSKSEMI 美森科







TVS



TSS



MOV



GDT



PIFF

NUP1105LT1G-MS

**Product specification** 





#### **Features**

- 350 Watts peak pulse power (tp = 8/20µs)
- Unidirectional and unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 ±20kV contact ±20kV air
- IEC 61000-4-4 (EFT) 40A (5 /50ns)
- IEC 61000-4-5 (Lightning) 8A (8/20µs)

# **Application**

- Dataline
- Automatic Teller Machines
- Net works
- Power line

#### **Mechanical Data**

SOT-23 package

Molding compound flammability rating: UL 94V-0

Packaging: Tape and Reel RoHS/WEEE Compliant

#### **Reference News**

PACKAGE OUTLINE	Pin Configuration	Marking	
SOT-23	2 3	27 <u>H</u> *	



## **Absolute Maximum Rating**

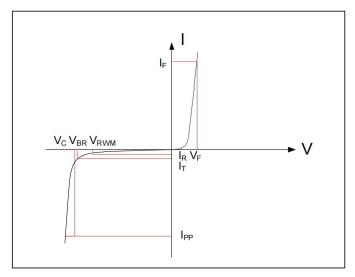
Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>p</sub> =8/20μs )	P <sub>PP</sub>	350	Watts
Peak Pulse Current ( t <sub>p</sub> =8/20μs ) (note1)	$I_{pp}$	8	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$ m V_{ESD}$	20 20	kV
Lead Soldering Temperature	$T_{L}$	260(10seconds)	$^{\circ}$
Junction Temperature	$T_{\rm J}$	-55 to + 125	$^{\circ}$
Storage Temperature	$T_{ m stg}$	-55 to + 125	$^{\circ}$

## **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$		24		26	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	25			V
Reverse Leakage Current	$I_R$	$V_{RWM}$ =24V,T=25C			1.0	μА
Peak Pulse Current	$I_{PP}$	tp=8/20μs			8	A
Clamping Voltage	$V_{\rm C}$	$I_{PP}=8A, t_p=8/20 \mu s$		44		V
Junction Capacitance	C <sub>j</sub>	$V_R = 0V$ , $f = 1MHz$ (Pin 1 to Pin 2)		30		pF

# **Electrical Parameters (TA = 25°C unless otherwise noted)**

Symbol	Parameter		
PP	Maximum Reverse Peak Pulse Current		
С	Clamping Voltage @ IPP		
RWM	Working Peak Reverse Voltage		
R	Maximum Reverse Leakage Current @ VRWM		
BR	Breakdown Voltage @ IT		
Т	Test Current		

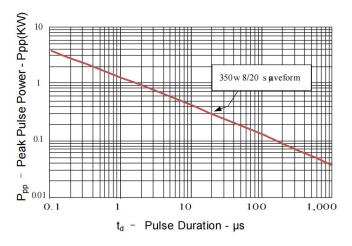


Note:. 8/20µs pulse waveform



## **Typical Characteristics**

Figure 1: Peak Pulse Power vs. Pulse Time



**Figure 2: Power Derating Curve** 

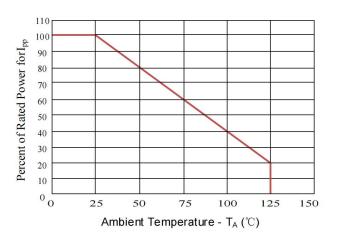


Figure3: Pulse Waveform

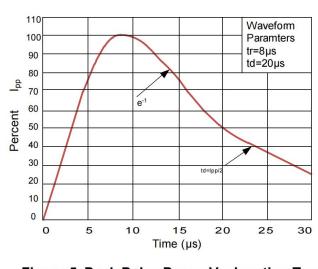


Figure 4: Clamping Voltage vs.lpp

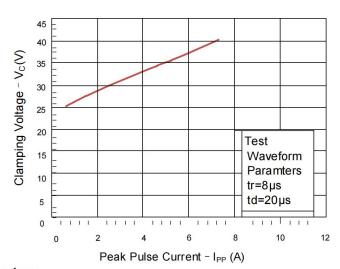
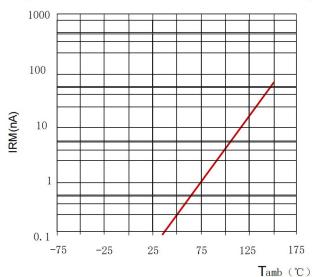
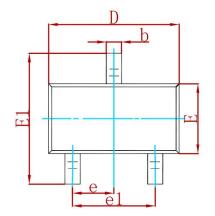


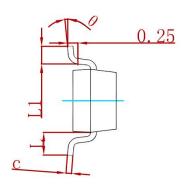
Figure 5: Peak Pulse Power Vs Junction Temperature

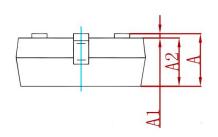




### PACKAGE MECHANICAL DATA

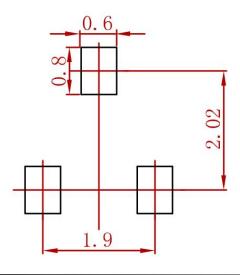






Symbol	Dimensions In Millimeters		Dimensions In Inches	
Syllibol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

# **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

### **REEL SPECIFICATION**

P/N	PKG	QTY
NUP1105LT1G-MS	SOT-23	3000



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